

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently amended) An etching method for etching an organic etching target film, the method comprising:

forming the organic etching target film on a protective film placed inside an airtight processing chamber, the organic etching film containing Si;

introducing a processing gas into the airtight processing chamber, the processing gas containing  $N_2$  and  $CF_4$  and ~~at least one of  $C_4F_8$  and  $CF_4$~~ ;

generating a plasma in the airtight processing chamber for etching the organic etching target film; and

etching the organic etching target film until the protective film is exposed, wherein a resist layer is used as a mask on the organic etching target film, wherein the etching process ceases once the protective film is exposed, and wherein the processing gas has a selection ratio greater than approximately 2.0, the selection ratio defined by an etching rate of the organic etching target film divided by an etching rate of the resist layer.

2. (Previously presented) The etching method according to claim 1, wherein the organic etching target film is constituted of  $SiO_2$  containing C and H.

3. (Previously presented) The etching method according to claim 1, wherein a dielectric constant of the organic etching target film is equal to or lower than 3.0.

4. (Previously presented) The etching method according to claim 1, wherein the organic etching target film is an organic polysiloxane film.

5. (Previously presented) The etching method according to claim 1, wherein the processing gas further contains Ar.

6-13. (Canceled)

14. (Currently amended) An etching method for etching an organic etching target film, the method comprising:

forming the organic etching target film on a protective film placed inside an airtight processing chamber, the organic etching film containing Si;

introducing a processing gas into the airtight processing chamber, the processing gas containing at least  $\text{CF}_4$  and  $\text{N}_2$ ;

generating a plasma in the airtight processing chamber for etching the organic etching target film; and

etching the organic etching target film until the protective film is exposed, wherein a resist layer is used as a mask on the organic etching target film, wherein the etching process ceases once the protective film is exposed,

wherein a flow rate ratio of  $\text{CF}_4$  and  $\text{N}_2$  in the processing gas is set within a following range: of  $1 \leq (\text{N}_2 \text{ flow rate} / \text{CF}_4 \text{ flow rate}) \leq 4$  ( $\text{N}_2 \text{ flow rate} / \text{CF}_4 \text{ flow rate}) \geq 1$  to prevent an occurrence of an etching stop and ( $\text{N}_2 \text{ flow rate} / \text{CF}_4 \text{ flow rate}) \leq 4$  to prevent an occurrence of bowing.

15-17. (Canceled)

18. (New) An etching method for etching an organic etching target film, the method comprising:

forming the organic etching target film on a protective film placed inside an airtight processing chamber, the organic etching film containing Si;

introducing a processing gas into the airtight processing chamber, the processing gas containing  $\text{N}_2$  and  $\text{C}_4\text{F}_8$ ;

generating a plasma in the airtight processing chamber for etching the organic etching target film; and

etching the organic etching target film until the protective film is exposed,

wherein a resist layer is used as a mask on the organic etching target film,

wherein the etching process ceases once the protective film is exposed,

wherein the processing gas has a selection ratio greater than approximately 2.0, the selection ratio defined by an etching rate of the organic etching target film divided by an etching rate of the resist layer, and

wherein a flow rate ratio of  $\text{N}_2$  and  $\text{C}_4\text{F}_8$  in the processing gas is set within a range of  $(\text{N}_2 \text{ flow rate} / \text{C}_4\text{F}_8 \text{ flow rate}) \geq 10$  to prevent an occurrence of an etching stop.